

## TC74AC240,241,244 Octal Bus Buffers

240: Inverted, 3-State Outputs  
241: Non-Inverted, 3-State Outputs  
244: Non-Inverted, 3-State Outputs

### Features:

- **High Speed:**  $t_{pd} = 4.0\text{ns}$  (typ.) at  $V_{CC} = 5\text{V}$
- **Low Power Dissipation:**  $I_{CC} = 8\mu\text{A}$  (max.) at  $T_a = 25^\circ\text{C}$
- **High Noise Immunity:**  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min.)
- **Symmetrical Output Impedance:**  $I_{OH} = I_{OL} = 24\text{mA}$  (min.). Capability of driving  $50\Omega$  transmission lines.
- **Balanced Propagation Delays:**  $t_{PLH} = t_{PHL}$
- **Wide Operating Voltage Range:**  $V_{CC}(\text{opr}) = 2\text{V} \sim 5.5\text{V}$
- **Pin and Function Compatible with 74F240/241/244**
- **AC240 and AC244 Available in DIP, SOIC, SOP and SSOP Packages.**
- **AC241 Available in DIP, SOIC and SOP Packages.**

The TC74AC240, 241 and 244 are advanced high speed CMOS OCTAL BUS BUFFERS fabricated with silicon gate and double-layer metal wiring CMOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL, while maintaining the CMOS low power dissipation.

The 74AC240 is an inverting 3-state buffer having two active-low output enables. The TC74AC241 and TC74AC244 are non-inverting 3-state buffers that differ only in that the 241 has one active-high and one active-low output enable, and the 244 has two active-low output enables.

These devices are designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### Truth Table

INPUTS			OUTPUTS	
$\bar{G}$	$G^{\Delta}$	$A_n$	$Y_n$	$\bar{Y}_n^{\Delta\Delta}$
L	H	L	L	H
L	H	H	H	L
H	L	X	Z	Z

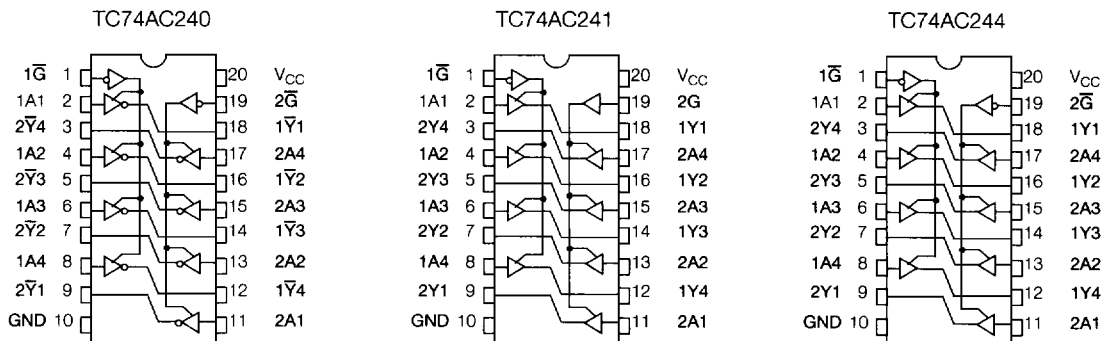
$\Delta$  : for TC74AC241 only

$\Delta\Delta$  : for TC74AC240 only

X : Don't Care

Z : High Impedance

### Pin Assignment



## Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5-7.0	V
DC Input Voltage	$V_{IN}$	-0.5- $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5- $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	$\pm 20$	mA
Output Diode Current	$I_{OK}$	$\pm 50$	mA
DC Output Current	$I_{OUT}$	$\pm 50$	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	$\pm 200$	mA
Power Dissipation	$P_D$	500 (DIP) */180 (SOP)	mW
Storage Temperature	$T_{stg}$	-65-150	°C
Lead Temperature 10sec	$T_L$	300	°C

\* 500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ .  
From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  
-10mW/°C should be applied up to 300mW.

## Recommended Operating Conditions

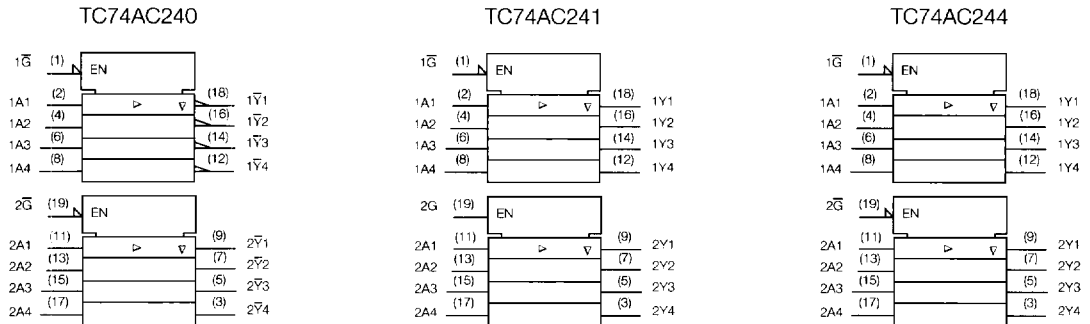
PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2.0-5.5	V
Input Voltage	$V_{IN}$	0- $V_{CC}$	V
Output Voltage	$V_{OUT}$	0- $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40-85	°C
Input Rise and Fall Time	dt/dv	0-100 ( $V_{CC} = 3.3 \pm 0.3\text{V}$ ) 0-20 ( $V_{CC} = 5 \pm 0.5\text{V}$ )	ns/v

## DC Electrical Characteristics

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT		
			$V_{CC}$	Min.	Typ.	Max.	Min.		Max.	
High-Level Input Voltage	$V_{IH}$	—	2.0	1.50	—	—	1.50	—	V	
			3.0	2.10	—	—	2.10	—		
			5.5	3.85	—	—	3.85	—		
Low-Level Input Voltage	$V_{IL}$	—	2.0	—	—	0.50	—	0.50	V	
			3.0	—	—	0.90	—	0.90		
			5.5	—	—	1.65	—	1.65		
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -50\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
				5.5	—	—	—	—	—	
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -4\text{mA}$	3.0	2.58	—	—	2.48	—	V
				4.5	3.94	—	—	3.80	—	
				5.5	—	—	—	3.85	—	
				5.5	—	—	—	3.85	—	
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -24\text{mA}$	3.0	2.58	—	—	2.48	—	V
				4.5	3.94	—	—	3.80	—	
				5.5	—	—	—	3.85	—	
				5.5	—	—	—	3.85	—	
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -75\text{mA}^*$	3.0	2.58	—	—	2.48	—	V
				4.5	3.94	—	—	3.80	—	
				5.5	—	—	—	3.85	—	
				5.5	—	—	—	3.85	—	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 50\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
				3.0	—	—	0.36	—	0.44	
				4.5	—	—	0.36	—	0.44	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 12\text{mA}$	3.0	—	—	0.36	—	0.44	V
				4.5	—	—	0.36	—	0.44	
				5.5	—	—	—	—	1.65	
				5.5	—	—	—	—	1.65	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 24\text{mA}$	3.0	—	—	0.36	—	0.44	V
				4.5	—	—	0.36	—	0.44	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 75\text{mA}^*$	3.0	—	—	—	—	1.65	V
				4.5	—	—	—	—	1.65	
3-State Output Off-State Current	$I_{OZ}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	5.5	—	—	$\pm 0.5$	—	$\pm 5.0$	$\mu\text{A}$	
			5.5	—	—	$\pm 0.5$	—	$\pm 5.0$		
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	$\pm 0.1$	—	$\pm 1.0$	$\mu\text{A}$	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	8.0	—	80.0	$\mu\text{A}$	

\* This spec indicates the capability of driving  $50\Omega$  transmission lines.  
One output should be tested at a time for a 10ms maximum duration.

## IEC Logic Symbol

AC Electrical Characteristics ( $C_L = 50\text{pF}$ ,  $R_L = 500\Omega$ , Input  $t_r = t_f = 3\text{ns}$ )

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40\text{--}85^\circ\text{C}$		UNIT		
			$V_{CC}$	Min.	Typ.	Max.	Min.		Max.	
Propagation Delay Time <sup>*(2)</sup>	$t_{pLH}$ $t_{pHL}$	—	3.3±0.3	—	6.3	10.5	1.0	ns		
			5.0±0.5	—	4.8	7.0	1.0		8.0	
Propagation Delay Time <sup>** (2)</sup>	$t_{pLH}$ $t_{pHL}$	—	3.3±0.3	—	7.0	11.4	1.0		ns	
			5.0±0.5	—	5.2	7.5	1.0			8.5
Output Enable Time	$t_{pZL}$ $t_{pZH}$	—	3.3±0.3	—	8.4	14.0	1.0			ns
			5.0±0.5	—	5.9	8.7	1.0			
Output Disable Time	$t_{pLZ}$ $t_{pHZ}$	—	3.3±0.3	—	6.4	10.5	1.0	ns		
			5.0±0.5	—	5.5	7.9	1.0			
Input Capacitance	$C_{IN}$	—	—	5	10	—	pF			
Output Capacitance	$C_{OUT}$	—	—	10	—	—				
Power Dissipation Capacitance	$C_{PD}^{\dagger}$	—	—	30	—	—				

Note (1):  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(oper)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8(\text{per bit})$ .

(2): \* For TC74AC240 only.

\*\* For TC74AC241/244 only.